

V1.1 Datasheet

N-Channel 40V MOSFET

FEATURES

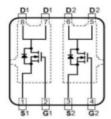
- ●Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

PRODU	CTY SU	MMARY
V_{DS}	R _{DS(o}	_{n)} m(Ω) Max
40	18	@V _{GS} =10V
40	22	@V _{GS} =4.5V

Application

- ●Portable Devices
- ■Consumer Electronics

DFN3333



Mechanical

●Case:DFN3333 Package

Packing Information

Package	Packing
DFN3333	5Kpcs/13"Reel

Maximum Ratings (T _A =25°C u	Maximum Ratings (T _A =25°C unless otherwise specified)												
Parameter	Symbol	Limit	Unit										
Drain-Source Voltage	V _{DS}	40	V										
Gate-Source Voltage	V_{GS}	±20	V										
Continuous Drain Current 1)	I _D	15	Α										
Continuous Drain Current 4)	I _{DM}	60	Α										
Maximum Power Dissipation	P _D	5	W										
Operating Junction and Storage Temperature Range	T _J , T _{STG}	-55 to 150	°C										

Typical Thermal Re	sistance		
Parameter	Symbol	Limit	Unit
Junction-to-Ambient Thermal Resistance 3)	$R_{\theta JA}$	34	°C/W

Note:

- 1. Pulse width<300us, Duty cycle<2%.
- 2. Fused current that based on wire numbers and diameter.
- 3. Guaranteed by design, not subject to production testing.
- 4. The maximum current rating is package limited.
- 5. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$ =150°C. Ratings are based on low frequency and duty cycles to keepinitial T_J =25°C.

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Electrical Cha	racteristics	(T _A =25°C UNLESS OTH	ERWISE	NOTED)	
Characteristics	Symbol	Test Condition		Limits		Unit
Characteristics	Symbol	rest Condition	Min	Тур	Max	Unit
		Static				
Drain-Source Breakdown Voltage	B _{VDSS}	V_{GS} =0V, I_D =250uA	40	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=250uA$	1.0	1.6	2.0	V
Drain-Source On-State Resistance	D	V _{GS} =10V, I _D =18A	-	15	18	mΩ
Dialii-Source Off-State Resistance	$R_{DS(on)}$	V_{GS} =4.5V, I_D =16A	-	19	22	mΩ
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =40V, V _{GS} =0V	-	-	1	uA
GateSource Leakage Current	I _{GSS}	V_{GS} =±20V, V_{DS} =0V	-	-	±100	nA

	D	rainSource Diode				
Maximum Continuous Body Diode Forward Current	I _S	-	-	-	1.2	А
Diode Forward Voltage	V _{SD}	I _S =1.0A, V _{GS} =0V	-	-	1.5	V

Note

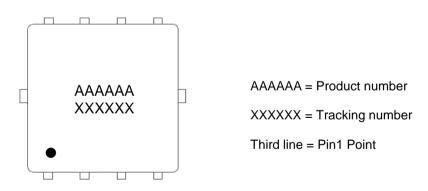
- 1. Pulse width<300us, Duty cycle<2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$ =150°C. Ratings are based on low frequency and duty cycles to keep initial T_J =25°C.
- 4. The maximum current rating is package limited.
- 5. R_{QJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch2 with 2oz.square pad of copper.
- 6. Guaranteed by design, not subject to production testing.



Package Outline Dimensions (inches and millimeters)

ži	DF	N333	33	
		Dime	nsions	
SYMBOL	Millin	neters	Inc	hes
	Min	Max	Min	Max
Α	0.70	0.80	0.03	0.03
b	0.25	0.35	0.01	0.01
С	0.10	0.25	0.00	0.01
D	3.25	3.45	0.13	0.14
D1	3.00	3.20	0.12	0.13
D2	1.78	1.98	0.07	0.08
D3		0.13	(15)	0.01
E	3.20	3.40	0.13	0.13
E1	3.00	3.20	0.12	0.13
E2	2.39	2.59	0.09	0.10
е		0.65	BSC	
Н	0.30	0.50	0.01	0.02
L	0.30	0.50	0.01	0.02
L1	0.	13	1020	0.005
K	0.30		0.01	
θ	-	12	5±1	12
M		0.15	844	0.01

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